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Please note: As part of the Fairchild Semiconductor integration, some of the Fairchild orderable part numbers will need to change in order to meet ON Semiconductor's system requirements. Since the ON Semiconductor product management systems do not have the ability to manage part nomenclature that utilizes an underscore (_), the underscore (_) in the Fairchild part numbers will be changed to a dash (-). This document may contain device numbers with an underscore (_). Please check the ON Semiconductor website to verify the updated device numbers. The most current and up-to-date ordering information can be found at www.onsemi.com. Please email any questions regarding the system integration to Fairchild guestions@onsemi.com.

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FGH40N60SMD_F085 600V, 40A Field Stop IGBT

Features

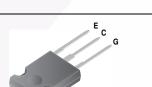
- Maximum Junction Temperature: T_J = 175°C
- · Positive Temperaure Co-efficient for easy parallel operating
- · High current capability
- Low saturation voltage: $V_{CE(sat)} = 1.9V(Typ.)$ @ $I_C = 40A$
- · High input impedance
- · Tightened Parameter Distribution
- · RoHS compliant
- · Qualified to Automotive Requirements of AEC-Q101



Using Novel Field Stop IGBT Technology, Fairchild's new series of Field Stop IGBTs offer the optimum performance for Automotive Chargers, Inverter, and other applications where low conduction and switching losses are essential.

Applications

- · Automotive chargers, Converters, High Voltage Auxiliaries
- Inverters, SMPS,PFC, UPS





Absolute Maximum Ratings

Symbol	Description		Ratings	Units
V _{CES}	Collector to Emitter Voltage		600	V
V _{GES}	Gate to Emitter Voltage		± 20	V
I _C	Collector Current	@ T _C = 25°C	80	Α
1.0	Collector Current	@ T _C = 100°C	40	Α
I _{CM (1)}	Pulsed Collector Current		120	Α
I _F	Diode Forward Current	@ T _C = 25°C	40	A
	Diode Forward Current	@ T _C = 100°C	20	A
I _{FM(1)}	Pulsed Diode Maximum Forward Current		120	A
P _D	Maximum Power Dissipation	$@ T_C = 25^{\circ}C$	349	W
. 0	Maximum Power Dissipation	@ T _C = 100°C	174	W
TJ	Operating Junction Temperature		-55 to +175	°C
T _{stg}	Storage Temperature Range		-55 to +175	°C
T _L	Maximum Lead Temp. for soldering Purposes, 1/8" from case for 5 second	ds	300	°C

Thermal Characteristics

Symbol	Parameter	Ratings	Units
$R_{\theta JC}(IGBT)_{(2)}$	Thermal Resistance, Junction to Case	0.43	°C/W
$R_{\theta JC}(Diode)$	Thermal Resistance, Junction to Case	1.8	°C/W

Symbol	Parameter	Тур.	Units	
$R_{ heta JA}$	Thermal Resistance, Junction to Ambient (PCB Mount)(2)	45	°C/W	

Package Marking and Ordering Information

Device Marking Device		Package	Packing Type	Qty per Tube	
FGH40N60SMD	FGH40N60SMD_F085	TO-247	Tube	30ea	

For Fairchild's definition of "green" Eco Status, please visit: http://www.fairchildsemi.com/company/green/rohs_green.html.

Electrical Characteristics of the IGBT T_C = 25°C unless otherwise noted

Symbol	Parameter	Test Conditions	Min.	Тур.	Max.	Units
Off Charac	eteristics					
BV _{CES}	Collector to Emitter Breakdown Voltage	$V_{GE} = 0V, I_{C} = 250uA$	600	-	-	V
$\frac{\Delta BV_{CES}}{\Delta T_{J}}$	Temperature Coefficient of Breakdown Voltage	V _{GE} = 0V, I _C = 250uA	-	0.6	-	V/°C
I _{CES}	Collector Cut-Off Current	$V_{CE} = V_{CES}, V_{GE} = 0V$	-	-	250	
		I _{CES} at 80%*B _{VCES} , 175°C	-	-	800	μΑ
I _{GES}	G-E Leakage Current	$V_{GE} = V_{GES}, V_{CE} = 0V$	-	-	±400	nA
On Charac	teristics					
V _{GE(th)}	G-E Threshold Voltage	$I_C = 250uA$, $V_{CE} = V_{GE}$	3.5	4.5	6.0	V
		$I_C = 40A, V_{GE} = 15V$	-	1.9	2.5	V
V _{CE(sat)}	Collector to Emitter Saturation Voltage	I _C = 40A, V _{GE} = 15V, T _C = 175°C	-	2.1	-	V
Dynamic C	Characteristics					
C _{ies}	Input Capacitance		-	1880	2500	pF
C _{oes}	Output Capacitance	$V_{CE} = 30V_{,} V_{GE} = 0V_{,}$ f = 1MHz	-	180	240	pF
C _{res}	Reverse Transfer Capacitance	1 = 11/11/12	-	50	65	pF
Switching	Characteristics					
t _{d(on)}	Turn-On Delay Time		-	18	24	ns
t _r	Rise Time		-	28	36.4	ns
t _{d(off)}	Turn-Off Delay Time	$V_{CC} = 400V, I_{C} = 40A,$	-	110	143	ns
t _f	Fall Time	$R_G = 6\Omega$, $V_{GE} = 15V$,	-	13.2	18.5	ns
E _{on}	Turn-On Switching Loss	Inductive Load, T _C = 25°C	-	0.92	1.2	mJ
E _{off}	Turn-Off Switching Loss		-	0.3	0.39	mJ
E _{ts}	Total Switching Loss		-	1.22	1.59	mJ
t _{d(on)}	Turn-On Delay Time		-	16.7	23.8	ns
t _r	Rise Time		-	27	35.1	ns
t _{d(off)}	Turn-Off Delay Time	$V_{CC} = 400V, I_{C} = 40A,$	-	116	151	ns
t _f	Fall Time	$R_G = 6\Omega$, $V_{GE} = 15V$,	-	56.5	81	ns
E _{on}	Turn-On Switching Loss	Inductive Load, T _C = 175°C	-	1.47	1.91	mJ
E _{off}	Turn-Off Switching Loss		-	0.73	0.95	mJ
E _{ts}	Total Switching Loss		_	2.20	2.86	mJ

Notes:

2:Rthjc for TO-247: according to Mil standard 883-1012 test method. Rthja for TO-247: according to JESD51-2, test method environmental condition and JESD51-10, test boards for through hole perimeter leaded package thermal measurements. JESD51-3: Low Effective Thermal Conductivity Test Board for Leaded Surface Mount Package.

^{1:}Repetitive rating: Pulse width limited by max junction temperature.

Electrical Characteristics of the IGBT (Continued)

Symbol	Parameter	Test Conditions	Min.	Тур.	Max	Units
Q_g	Total Gate Charge		-	119	180	nC
Q _{ge}	Gate to Emitter Charge	$V_{CE} = 400V, I_{C} = 40A,$ $V_{GE} = 15V$	-	13	20	nC
Q_{gc}	Gate to Collector Charge	VGE - 10V	-	58	90	nC

Electrical Characteristics of the Diode $T_C = 25^{\circ}C$ unless otherwise noted

Symbol	Parameter	Test Conditio	ns	Min.	Тур.	Max	Units
V _{FM}	Diode Forward Voltage	I _E = 20A	$T_{\rm C} = 25^{\rm o}{\rm C}$	-	2.3	2.8	V
FIVI	2.000 r o.mara romago		$T_{\rm C} = 175^{\rm o}{\rm C}$	-	1.67	-]
E _{rec}	Reverse Recovery Energy		$T_{\rm C} = 175^{\rm o}{\rm C}$	-	48.9	-	uJ
t	Diode Reverse Recovery Time	$I_{\rm F} = 20$ A, $dI_{\rm F}/dt = 200$ A/µs	$T_{\rm C} = 25^{\rm o}{\rm C}$	-	36	47	ns
^L rr	2.000 1.010.00 1.00010.) 1	ης -207, αιριαί - 2007/μ3	$T_{\rm C} = 175^{\rm o}{\rm C}$	-	110	-	
Q _{rr}	Diode Reverse Recovery Charge		$T_{\rm C} = 25^{\rm o}{\rm C}$	-	46.8	61	nC
~II	2.000 No. 00 No. 00 No. 1000 Vol. y Onlargo		$T_{\rm C} = 175^{\rm o}{\rm C}$	-	470	-	

Figure 1. Typical Output Characteristics

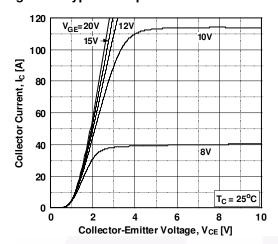


Figure 3. Typical Saturation Voltage Characteristics

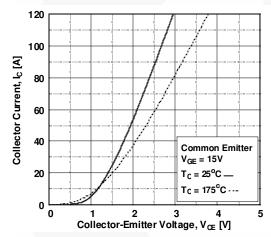


Figure 5. Saturation Voltage vs. Case
Temperature at Variant Current Level

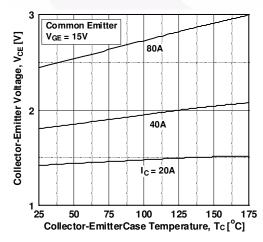


Figure 2. Typical Output Characteristics

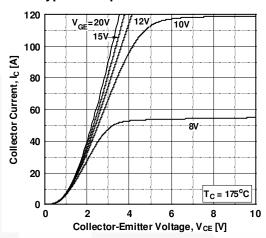


Figure 4. Transfer Characteristics

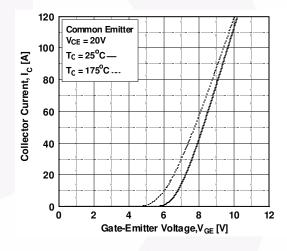


Figure 6. Saturation Voltage vs. V_{GE}

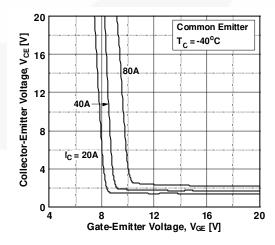


Figure 7. Saturation Voltage vs. V_{GE}

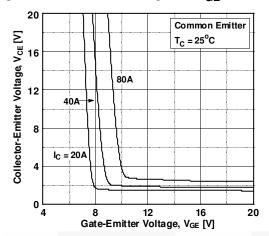


Figure 9. Capacitance Characteristics

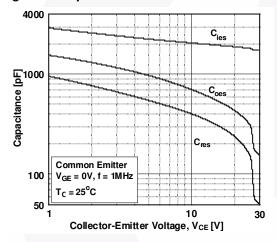


Figure 11. SOA Characteristics

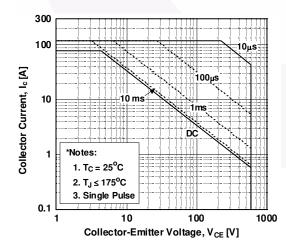


Figure 8. Saturation Voltage vs. V_{GE}

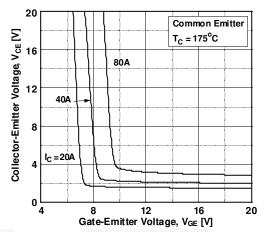


Figure 10. Gate charge Characteristics

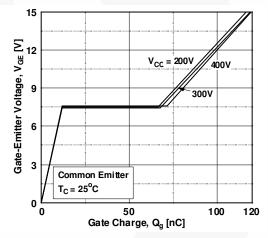


Figure 12. Turn-on Characteristics vs.
Gate Resistance

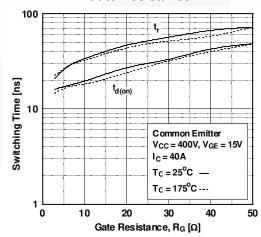


Figure 13. Turn-off Characteristics vs. Gate Resistance

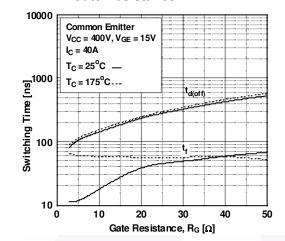


Figure 15. Turn-off Characteristics vs. Collector Current

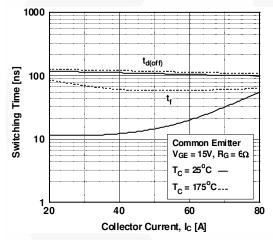


Figure 17. Switching Loss vs. Collector Current

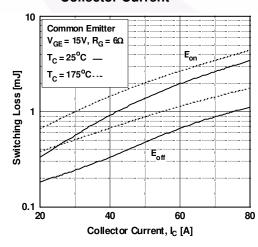


Figure 14. Turn-on Characteristics vs.
Collector Current

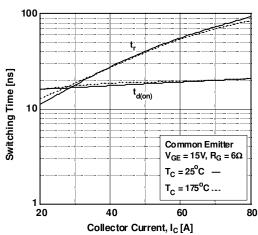


Figure 16. Switching Loss vs.
Gate Resistance

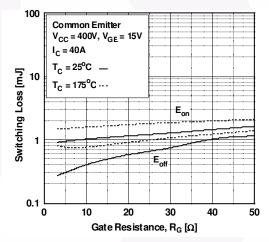


Figure 18. Turn off Switching SOA Characteristics

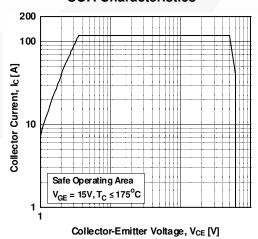


Figure 19. Current Derating

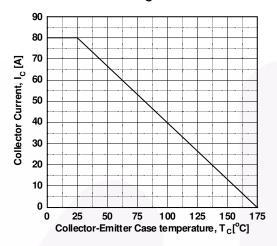


Figure 21. Forward Characteristics

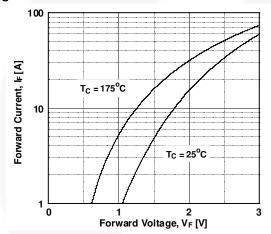


Figure 23. Stored Charge

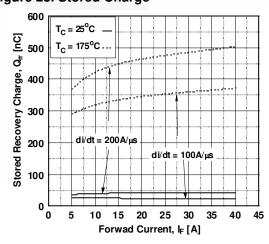


Figure 20. Load Current Vs. Frequency

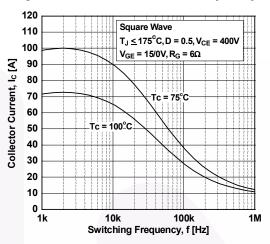


Figure 22. Reverse Current

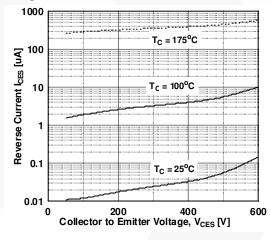


Figure 24. Reverse Recovery Time

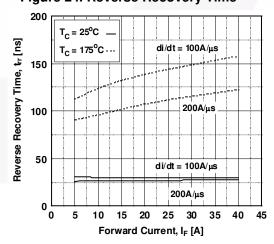


Figure 25. Transient Thermal Impedance of IGBT

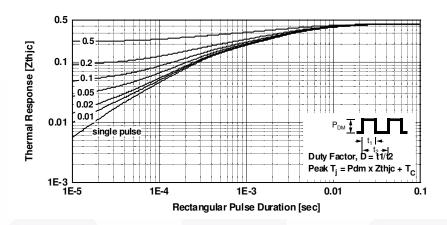
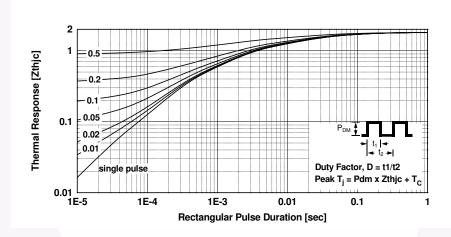
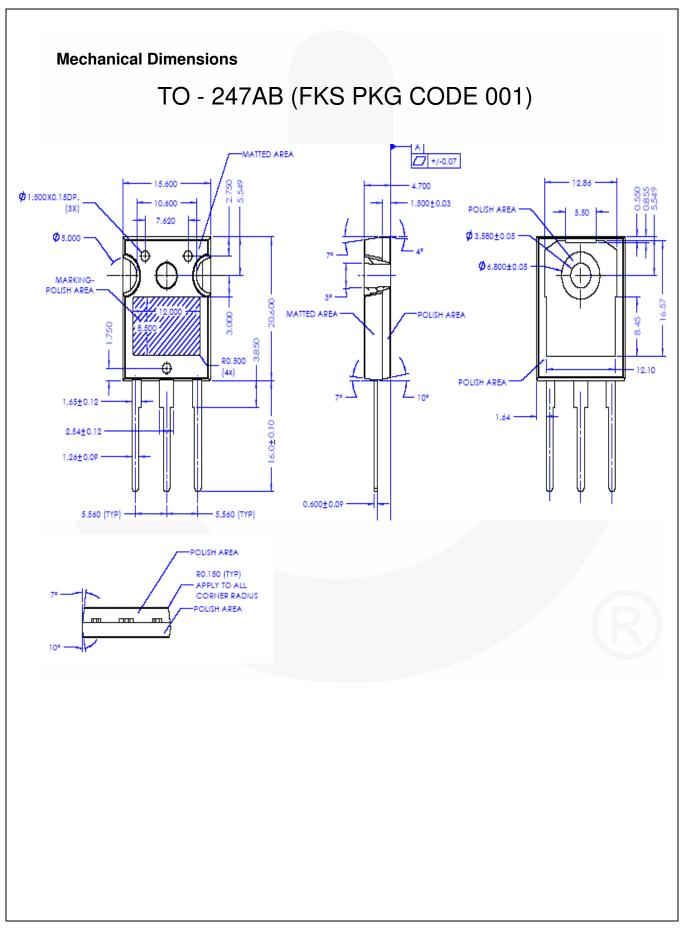


Figure 26.Transient Thermal Impedance of Diode









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